

◆ Features & Applications

- TrenchFET Power MOSFET.
- Super high dense cell design.
- Battery management, High speed switch, low power DC to DC converter.

◆ Absolute Maximum Ratings(Ta=25°C)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±10	V
I _D	Continuous Drain Current	2.3	A
I _S	Continuous Source-Drain Current(Diode Conduction)	0.6	A
P _D	Power Dissipation	400	mW
R _{θJA}	Thermal Resistance From Junction To Ambient (t≤5s)	300	°C/W
T _J , T _{stg}	Operation Junction And Storage Temperature Range	-55~+150	°C

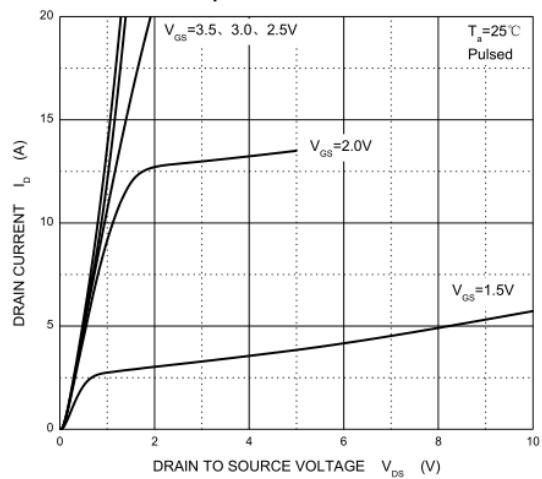
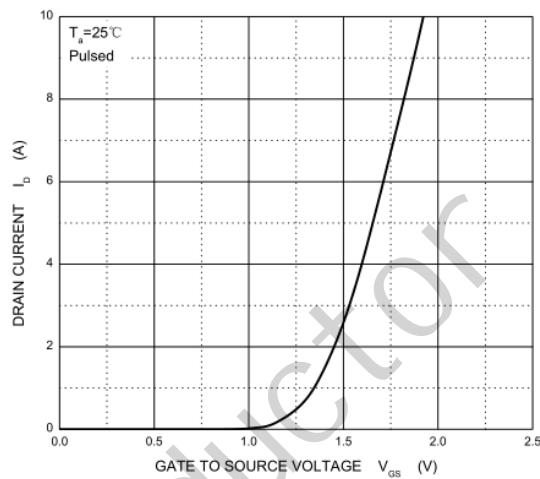
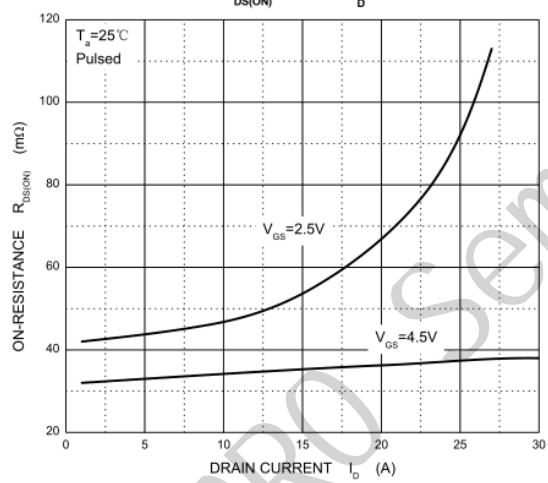
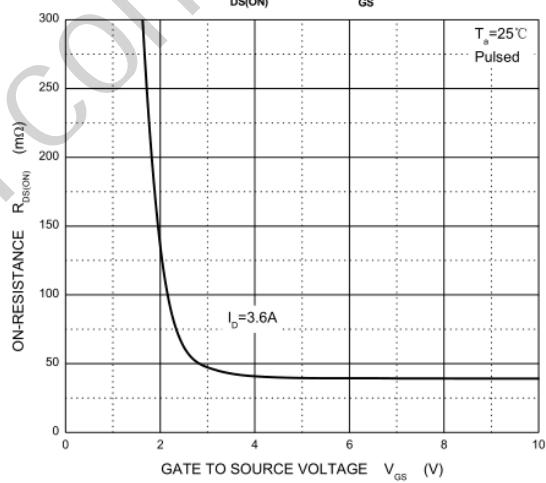
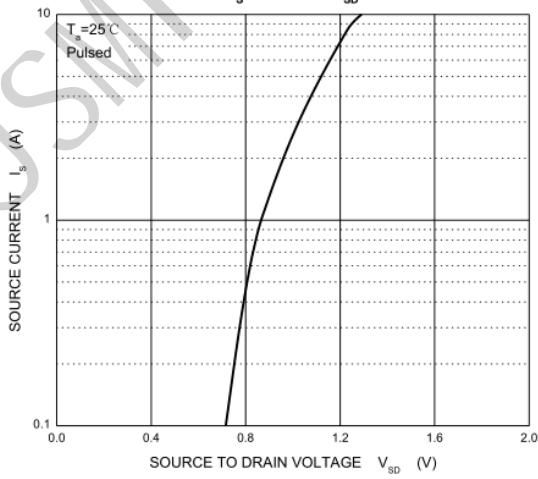
◆ Electrical Characteristics (Ta=25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} =0, I _D =10μA	20			V
V _{GS(th)}	Gate-threshold voltage	V _{DS} =V _{GS} , I _D =250μA	0.6		1.1	V
I _{GSS}	Collector cut-off current	V _{DS} =0, V _{GS} =±10V			100	nA
I _{DSS}	Collector cut-off current	V _{DS} =20V, V _{GS} =0V			1	μA
R _{DS(on)}	Drain-source on-resistance ^a	V _{GS} =4.5V, I _D =2A		50	60	mΩ
		V _{GS} =2.5V, I _D =1A		65	85	mΩ
g _{FS}	Forward transconductance ^a	V _{DS} =5V, I _D =2.5A		10		S
V _{SD}	Diode forward voltage	I _S =1A, V _{GS} =0V			1.2	V
Dynamic						
Q _g	Total gate charge	V _{DS} =10V, V _{GS} =4.5V, I _D =2.5A		5.0	10	nC
Q _{gs}	Gate-source charge			0.65		
Q _{gd}	Gate-drain charge			1.5		
C _{iss}	Input capacitance ^b	V _{DS} =10V, V _{GS} =0V, f=1MHz		340		pF
C _{oss}	Output capacitance ^b			120		
C _{rss}	Reverse transfer capacitance ^b			80		
Switching^b						
t _{d(on)}	Turn-on delay time	V _{DS} =10V, RL=5.5Ω, I _D ≈2.5A, V _{GEN} =4.5V, R _g =6Ω		12		nS
t _r	Rise time			36		
t _{d(off)}	Turn-off delay time			34		
t _f	Fall time			10		

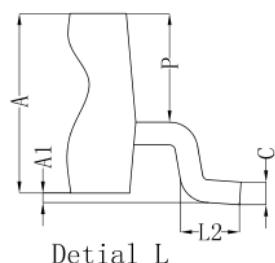
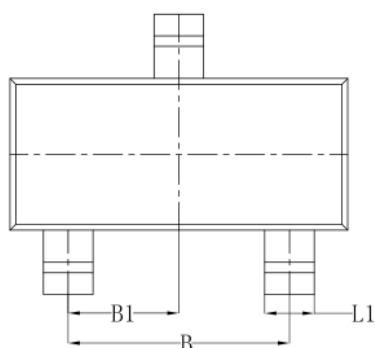
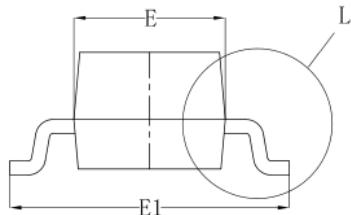
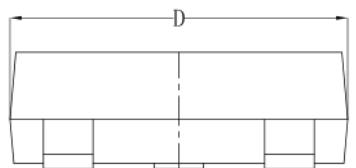
Notes :

- a. Pulse Test : Pulse width≤300μs, duty cycle ≤2%.
- b. These parameters have no way to verify.

◆ Typical Characteristics

Output Characteristics

Transfer Characteristics

 $R_{DS(ON)}$ — I_D

 $R_{DS(ON)}$ — V_{GS}

 I_S — V_{SD}


◆ SOT-23 Package Outline Dimensions



Symbol	Dim in mm		
	Min	Nom	Max
A	0.900	1.000	1.100
A1	0.000	0.050	0.100
B	1.800	1.900	2.000
B1	0.950 TYP		
C	0.100	0.110	0.120
D	2.800	2.900	3.000
E	1.250	1.300	1.350
E1	2.250	2.400	2.550
L1	0.350	0.400	0.500
L2	0.200	0.350	0.450
P	0.550	0.575	0.600

◆ Packaging SPEC.

Units				
Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box
3,000	15	45,000	4	180,000
Reel Dimension (unit: mm ³)				
Inner Box		Outer Box		
7" x 8	190x190x190	400x400x210		

◆ Marking

